



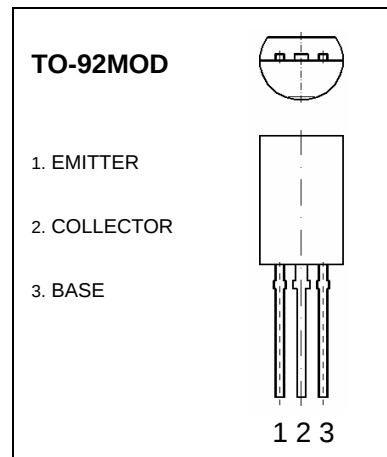
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SA817A TRANSISTOR (PNP)

FEATURES

- Complementary to 2SC1627A.
- Driver Stage Application of 30 to 35 Watts Amplifiers.



MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-400	mA
P_C	Collector Power Dissipation	800	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN		MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu\text{A}$, $I_E = 0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -5 \text{ mA}$, $I_B = 0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50 \text{ V}$, $I_E = 0$			-0.1	μA
Collector cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}$, $I_B = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2 \text{ V}$, $I_C = -50 \text{ mA}$	70		240	
	$h_{FE(2)}$	$V_{CE} = -2 \text{ V}$, $I_C = -200 \text{ mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -200 \text{ mA}$, $I_B = -20 \text{ mA}$			-0.4	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2 \text{ V}$, $I_C = -5 \text{ mA}$	-0.55		-0.8	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}$, $I_C = -10 \text{ mA}$		100		MHz
Out capacitance	C_{ob}	$V_{CB} = -10 \text{ V}$, $f = 1 \text{ MHz}$		14		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120 - 240

Typical Characteristics

2SA817A

